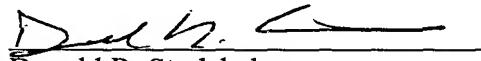


REMARKS

Please change paragraph 3 of the Remarks as follows.

Specifically, as can be seen from the foregoing amendments, independent claim 1 has been amended to recite a method of manufacturing an electronic device comprising the steps of (a) forming on an underlying layer an insulating film made from one of an oxide film, a nitride film, an oxide nitride film, an organic film and an organic-inorganic hybrid film; (b) forming a resist pattern on the insulating film; (c) forming an insulating film pattern by etching the insulating film with the resist pattern used as a mask; (d) conducting a plasma treatment on exposed portions of the underlying layer and the insulating film pattern without removing the resist pattern after step (c) and (e) forming a pattern for the underlying layer by etching the underlying layer with the resist pattern and the insulating film pattern used as a mask after step (d). That is, in accordance with the present invention, since the plasma treatment is conducted on exposed portions of the underlying layer and the insulating film pattern without removing the resist pattern in step (d), ~~etching foreign matters generated in small depositions generated on~~ the insulating film or underlying layer when forming the insulating film pattern the step (c) can be removed. Thereafter, since the pattern for the underlying layer is formed by etching the underlying layer with the resist pattern and the insulating film pattern used as a mask, the underlying layer pattern can be formed without being affected by the etching foreign matters and hence, with no pattern defect such as an increase in the size of pattern damage.

Respectfully submitted,


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